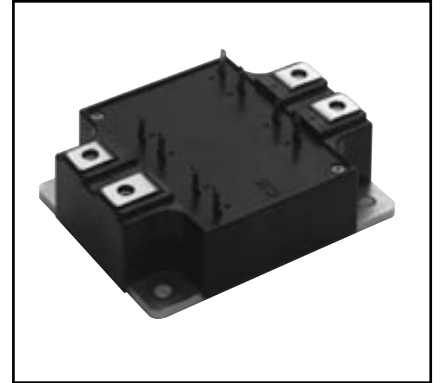
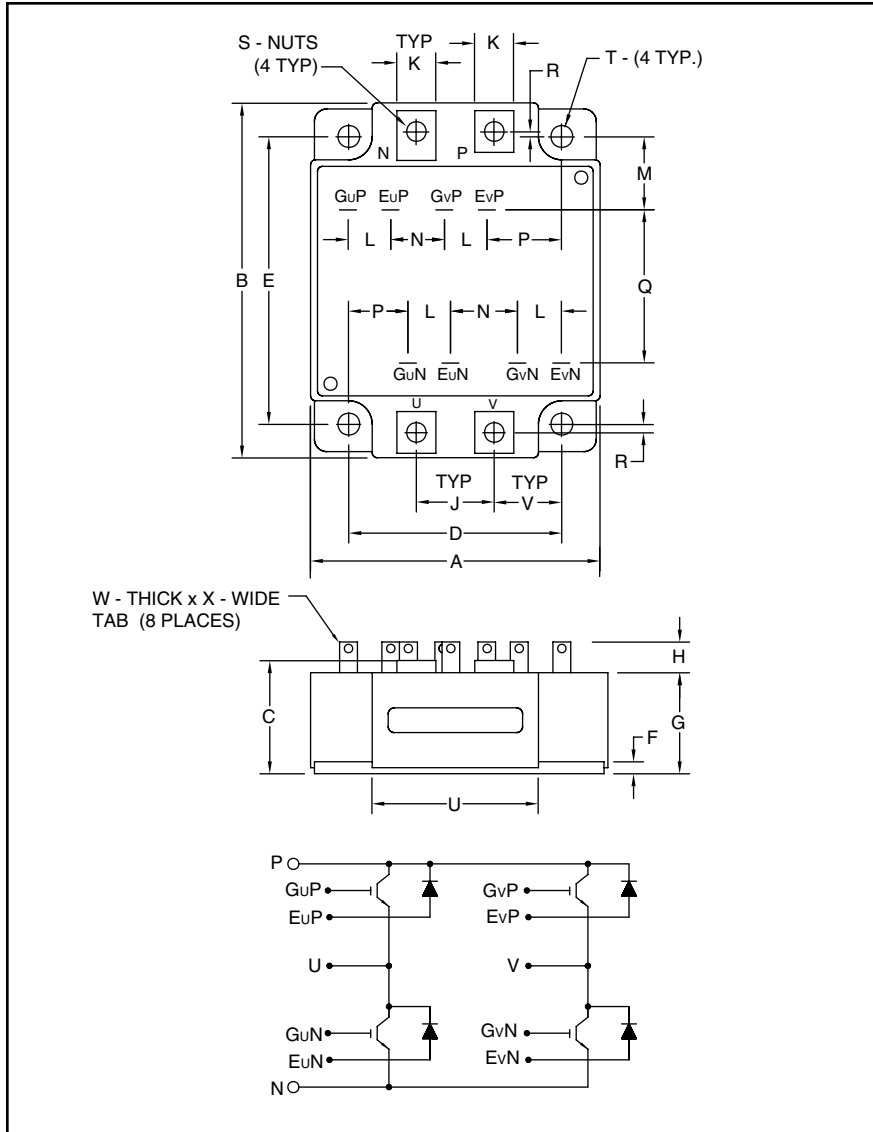


### Four IGBTMOD™ U-Series Module 100 Amperes/600 Volts



#### Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of four IGBT Transistors in an H-Bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

#### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery (70ns) Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

#### Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies
- Laser Power Supplies

#### Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM100BU-12H is a 600V ( $V_{CES}$ ), 100 Ampere Four-IGBT IGBTMOD™ Power Module.

#### Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	2.83	72.0
B	3.58	91.0
C	1.16 +0.04/-0.02	29.5 +1.0/-0.5
D	2.17±0.01	55.0±0.25
E	2.91±0.01	74.0±0.25
F	0.16	4.0
G	1.02	26.0
H	0.31	8.1
J	0.79	20.0
K	0.39	10.0
L	0.43	11.0

Dimensions	Inches	Millimeters
M	0.74	18.7
N	0.75	19.1
P	0.57	14.4
Q	1.55	39.3
R	0.05	1.25
S	M4	M4
T	0.22 Dia.	5.5 Dia.
U	1.61	41.0
V	0.69	17.5
W	0.02	0.5
X	0.110	2.79

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	100	12

**CM100BU-12H**  
**Four IGBTMOD™ U-Series Module**  
 100 Amperes/600 Volts

**Absolute Maximum Ratings,  $T_j = 25\text{ °C}$  unless otherwise specified**

Ratings	Symbol	CM100BU-12H	Units
Junction Temperature	$T_j$	-40 to 150	°C
Storage Temperature	$T_{stg}$	-40 to 125	°C
Collector-Emitter Voltage (G-E SHORT)	$V_{CES}$	600	Volts
Gate-Emitter Voltage (C-E SHORT)	$V_{GES}$	±20	Volts
Collector Current ( $T_c = 25\text{ °C}$ )	$I_C$	100	Amperes
Peak Collector Current ( $T_j \leq 150\text{ °C}$ )	$I_{CM}$	200*	Amperes
Emitter Current** ( $T_c = 25\text{ °C}$ )	$I_E$	100	Amperes
Peak Emitter Current**	$I_{EM}$	200*	Amperes
Maximum Collector Dissipation ( $T_c = 25\text{ °C}$ )	$P_c$	400	Watts
Mounting Torque, M4 Main Terminal	–	15	in-lb
Mounting Torque, M5 Mounting	–	31	in-lb
Weight	–	390	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{iso}$	2500	Volts

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

**Static Electrical Characteristics,  $T_j = 25\text{ °C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0V$	–	–	1	mA
Gate Leakage Current	$I_{GES}$	$V_{GE} = V_{GES}, V_{CE} = 0V$	–	–	0.5	µA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 10mA, V_{CE} = 10V$	4.5	6	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100A, V_{GE} = 15V, T_j = 25\text{ °C}$	–	2.4	3.0	Volts
		$I_C = 100A, V_{GE} = 15V, T_j = 125\text{ °C}$	–	2.6	–	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 300V, I_C = 100A, V_{GE} = 15V$	–	200	–	nC
Emitter-Collector Voltage*	$V_{EC}$	$I_E = 100A, V_{GE} = 0V$	–	–	2.6	Volts

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

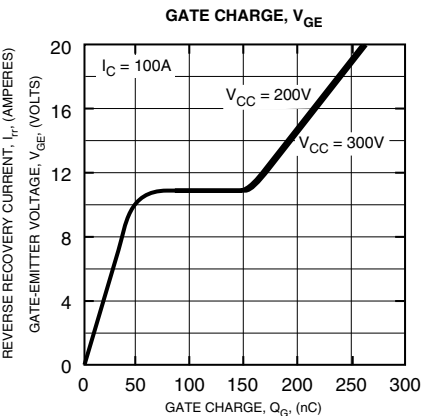
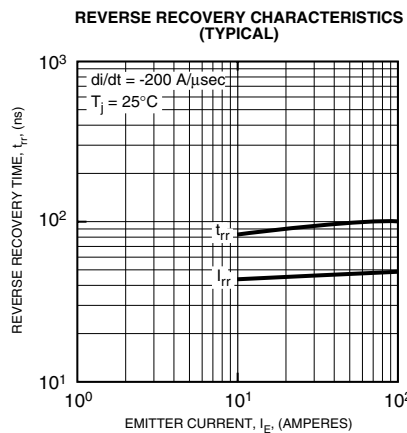
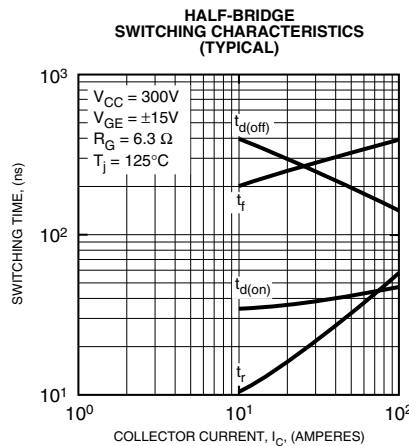
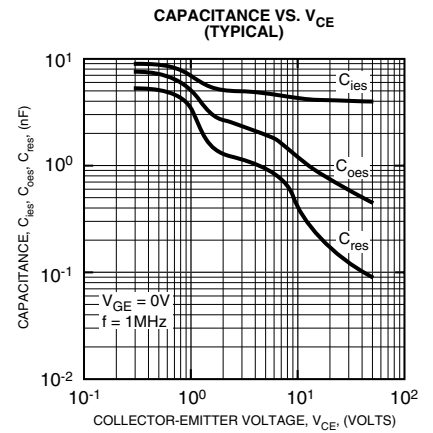
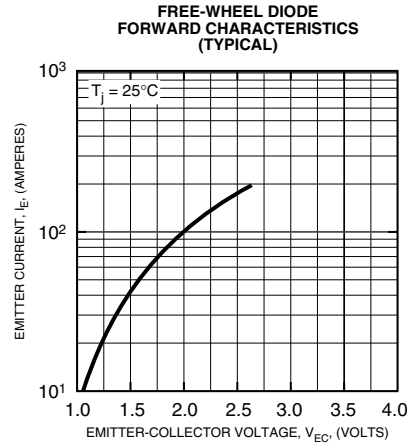
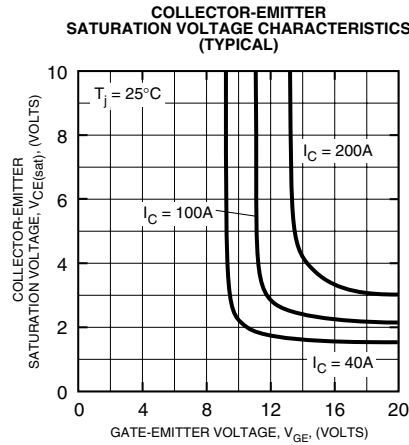
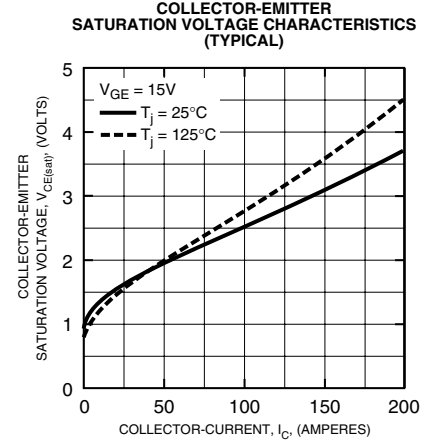
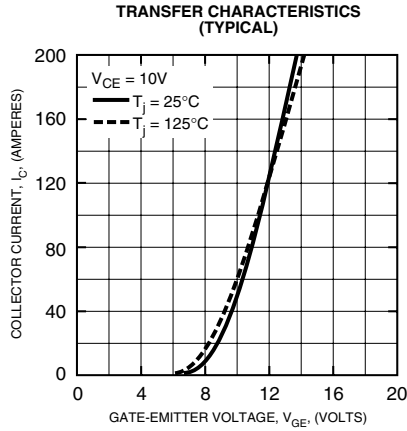
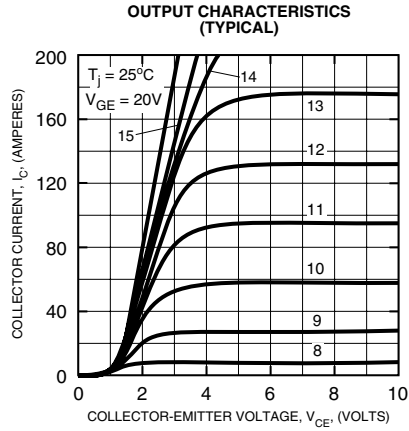
**Dynamic Electrical Characteristics,  $T_j = 25\text{ °C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units	
Input Capacitance	$C_{ies}$		–	–	8.8	nf	
Output Capacitance	$C_{oes}$	$V_{CE} = 10V, V_{GE} = 0V$	–	–	4.8	nf	
Reverse Transfer Capacitance	$C_{res}$		–	–	1.3	nf	
Resistive	Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 300V, I_C = 100A,$	–	–	100	ns
Load	Rise Time	$t_r$	$V_{GE1} = V_{GE2} = 15V,$	–	–	250	ns
Switch	Turn-off Delay Time	$t_{d(off)}$	$R_G = 6.3\Omega, \text{Resistive}$	–	–	200	ns
Times	Fall Time	$t_f$	Load Switching Operation	–	–	300	ns
Diode Reverse Recovery Time	$t_{rr}$	$I_E = 100A, di_E/dt = -200A/\mu s$	–	–	160	ns	
Diode Reverse Recovery Charge	$Q_{rr}$	$I_E = 100A, di_E/dt = -200A/\mu s$	–	0.24	–	µC	

**Thermal and Mechanical Characteristics,  $T_j = 25\text{ °C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/4 Module	–	–	0.31	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/4 Module	–	–	0.7	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.025	–	°C/W

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